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NTE6032 & NTE6033 Silicon Power Rectifier Diode 1000V, 40 Amp, DO5

Features:

- Fast Recovery Time
- Low Stored Charge
- Available in Cathode-to-Case (NTE6032) or Anode-to-Case (NTE6033) Style

Ratings and Characteristics:

Average Forward Current ($T_C = +75^\circ\text{C}$ Max), $I_{F(\text{AV})}$	40A
Maximum Repetitive Peak Reverse Voltage ($T_J = -40^\circ$ to $+125^\circ\text{C}$), V_{RRM}	1000V
Maximum Non-Repetitive Peak Reverse Voltage ($T_J = +25^\circ$ to $+125^\circ\text{C}$, $t_p \leq 5\text{ms}$), V_{RSM} ..	1250V
Maximum Reverse Current (At Rated V_R), I_R	
$T_J = +25^\circ\text{C}$	0.1mA
$T_J = +125^\circ\text{C}$	10mA
Maximum Forward Surge Current, I_{FSM}	
50Hz	700A
60Hz	730A
Fusing Current, I^2t	
50Hz	$2450\text{A}^2\text{s}$
60Hz	$2200\text{A}^2\text{s}$
Fusing Current, $I^2\sqrt{t}$	$34500\text{A}^2\sqrt{\text{s}}$
Operating Junction Temperature range, T_J	-40° to $+125^\circ\text{C}$
Storage Temperature range, T_{stg}	-40° to $+150^\circ\text{C}$
Thermal Resistance, Junction-to-Case (DC Operation), R_{thJC}	0.6°C/W
Thermal Resistance, Case-to-Sink (Surface flat, smooth, and greased), R_{thCS}	0.25°C/W
Maximum Mounting Torque (Non-lubricated threads), T	30 (3.3) in•lb (m•N)

Electrical Specifications:

Parameter	Symbol	Test Conditions		Rating	Unit	
Maximum Average Forward Current	I_F (AV)	180° sinusoidal condition, $T_C = +75^\circ\text{C}$ Max		40	A	
Maximum Peak One-Cycle Non-Repetitive Surge Current	I_{FSM}	$t = 10\text{ms}$	Half sinewave current, rated V_{RRM} reapplied, initial $T_J = +125^\circ\text{C}$	400	A	
		$t = 8.3\text{ms}$			420 A	
		$t = 10\text{ms}$	Half sinewave current, no voltage reapplied, initial $T_J = +125^\circ\text{C}$	475	A	
		$t = 8.3\text{ms}$			500 A	
Maximum I^2t for Fusing	I^2t	$t = 10\text{ms}$	Rated V_{RRM} reapplied, initial $T_J = +125^\circ\text{C}$	800	A^2s	
		$t = 8.3\text{ms}$			730 A^2s	
Maximum I^2t for Individual Device Fusing		$t = 10\text{ms}$	No voltage reapplied, initial $T_J = +125^\circ\text{C}$	1150	A^2s	
		$t = 8.3\text{ms}$			1050 A^2s	
Maximum $I^2\sqrt{t}$	$I^2\sqrt{t}$	$t = 0.1$ to 10ms , no voltage reapplied, Note 1		11500	$\text{A}^2\sqrt{t}$	
Maximum Peak Forward Voltage	V_{FM}	$T_J = +25^\circ\text{C}$, $I_{FM} = 125\text{A}$		1.95	V	
Maximum Reverse Recovery Time	t_{rr}	$T_J = +25^\circ\text{C}$, $I_F = 1\text{A}$ to $V_R = 30\text{V}$, $-dI_F/dt = 100\text{A}/\mu\text{s}$		350	ns	
		$T_J = +25^\circ\text{C}$, $I_F = 125\text{A}$, $-dI_F/dt = 25\text{A}/\mu\text{s}$		1000	ns	
Maximum Reverse Recovery Charge	Q_{RR}	$T_J = +25^\circ\text{C}$, $I_F = 1\text{A}$ to $V_R = 30\text{V}$, $-dI_F/dt = 100\text{A}/\mu\text{s}$		3100	nC	
		$T_J = +25^\circ\text{C}$, $I_F = 125\text{A}$, $-dI_F/dt = 25\text{A}/\mu\text{s}$		6000	nC	

Note 1. I^2t for time $t_x = I^2\sqrt{t} \bullet \sqrt{t_x}$.

